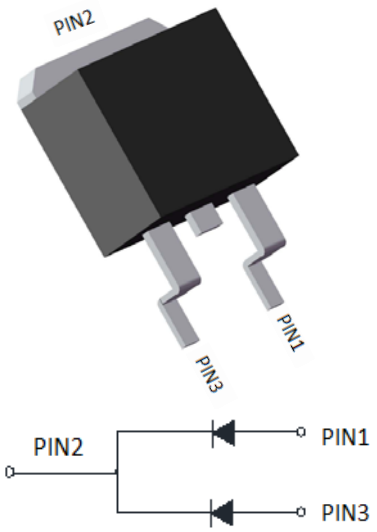
Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

- **Package**: TO-263
  Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals**: Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity**: As marked

■Maximum Ratings (Ta=25℃ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBRB30100CT	MBRB30150CT	MBRB30200CT
Device marking code			MBRB30100CT	MBRB30150CT	MBRB30200CT
Repetitive Peak Reverse Voltage	V_{RRM}	V	100	150	200
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25℃	I_O	A	30		
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25℃	I_{FSM}	A	250		
Current Squared Time @1ms≤t<8.3ms Tj=25℃,	I^2t	A^2s	262		
Storage Temperature	Tstg	℃	-55 ~ +175		
Junction Temperature	T_j	℃	-55 ~ +175		

■Electrical Characteristics (Ta=25℃ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRB30100CT	MBRB30150CT	MBRB30200CT
Maximum instantaneous forward voltage drop per diode	V_{FM}	V	I_{FM}=15.0A	0.8	0.85	0.9
Maximum DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	mA	$V_{RM}=V_{RRM}$ Ta=25℃	0.1		
	I_{RRM2}		$V_{RM}=V_{RRM}$ Ta=125℃	20		

■Thermal Characteristics （T_a=25℃ Unless otherwise specified）

PARAMETER		SYMBOL	UNIT	MBRB30100CT	MBRB30150CT	MBRB30200CT
Thermal Resistance	Between junction and case	$R_{\theta J-C}$	℃/W	2.0		

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBRB30100CT THRU MBRB30200CT	Approximate 1.43	50	2000	8000	Tube
MBRB30100CT THRU MBRB30200CT	Approximate 1.43	1000	2000	10000	Reel

■Characteristics (Typical)

FIG1:Io -Tc Curve

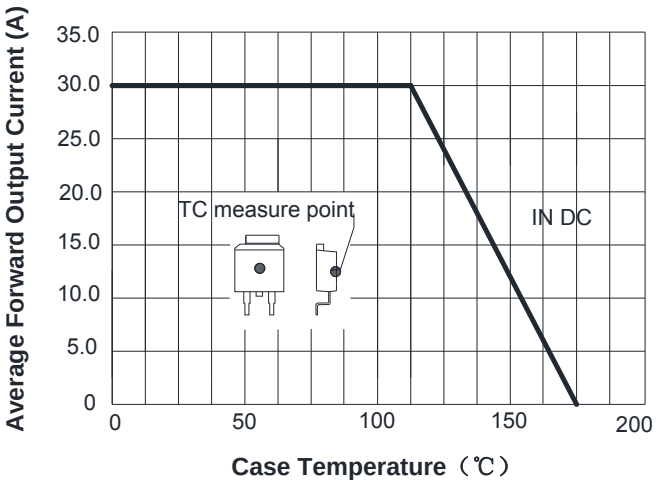


FIG2:Surge Forward Current Capability

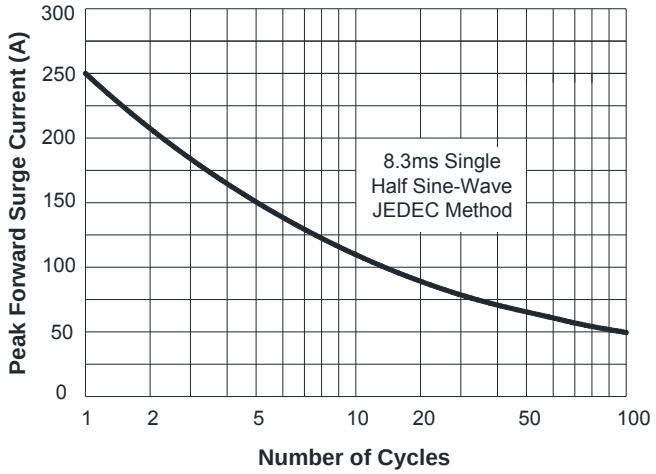


FIG3: Forward Voltage

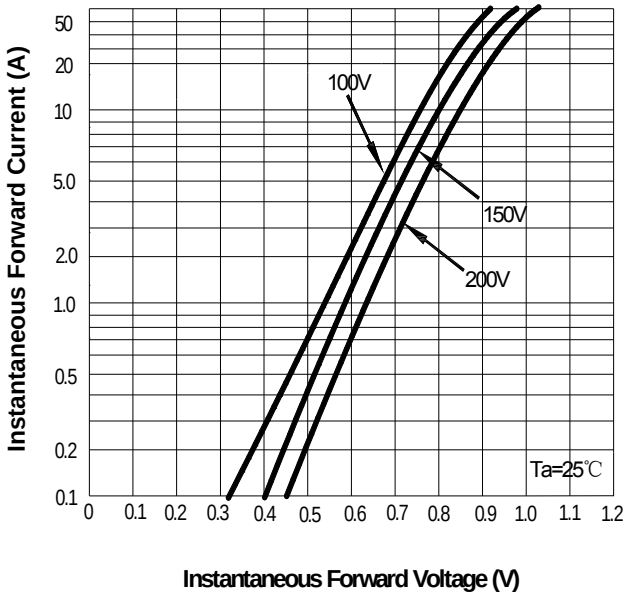
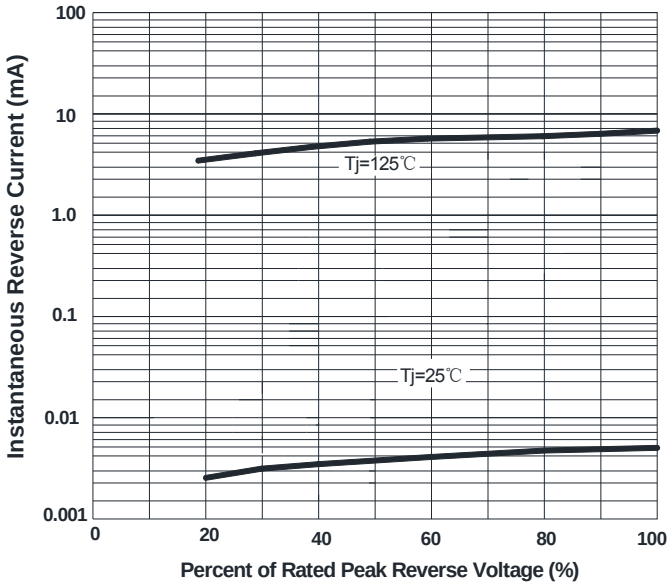
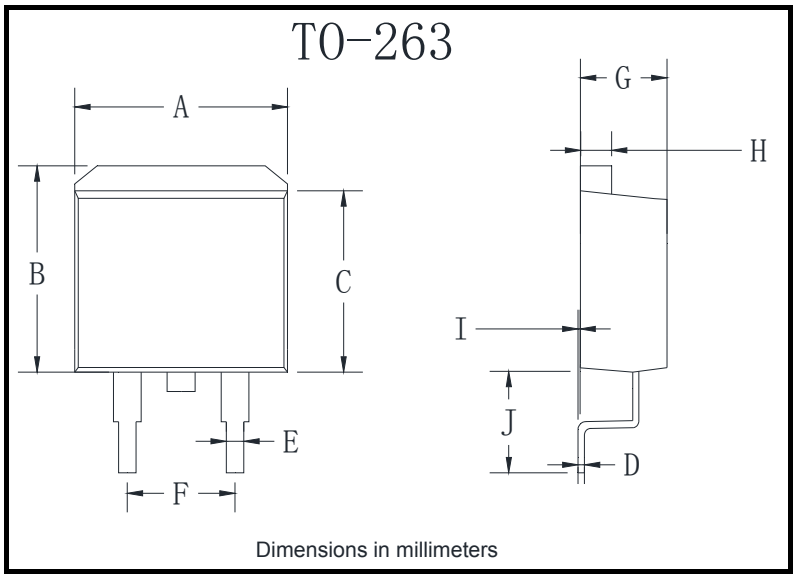


FIG.4: Instantaneous Reverse Characteristics



■Outline Dimensions



TO-263		
Dim	Min	Max
A	9.5	11.5
B	9.7	10.5
C	8.4	9.0
D	0.28	0.64
E	0.68	0.94
F	4.55	5.6
G	4.04	5.10
H	1.14	1.4
I	0	0.2
J	4.9	6.05

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